	Application No.	Applicant(s)	
Notice of Allowability	10/709,590	HUNG ET AL.	
	Examiner	Art Unit	
	Chuong A Luu	2825	
The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this app or other appropriate communication GHTS. This application is subject to	olication. If not include will be mailed in due	ed course. THIS
1. This communication is responsive to			
2. The allowed claim(s) is/are <u>16-20</u> .	•		
3. The drawings filed on 17 May 2004 are accepted by the Ex	xaminer.		
 4. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give 	e been received. e been received in Application No cuments have been received in this re- of this communication to file a reply of this application. itted. Note the attached EXAMINER'	national stage applica complying with the recomplying with the recomplyi	quirements
6. CORRECTED DRAWINGS (as "replacement sheets") mus		don is delicient.	
(a) ☐ including changes required by the Notice of Draftspers		948) attached	
1) hereto or 2) to Paper No./Mail Date			
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	s Amendment / Comment or in the O	ffice action of	
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the			back) of
7. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT			Note the
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date	5. Notice of Informal Pages No./Mail Data Paper No./Mail Data Pape	(PTO-413), e nent/Comment	·
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DETAILED ACTION

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

To The Specification

In the 11/22/2004 amendment to the specification entered in the IFW of this application, after "2003" insert –now U.S. Patent 6,770,934--.

Authorization for this examiner's amendment was given in a telephone interview with Mr. Jiawei Huang on November 24, 2004.

TO CLAIM

In claim 16, line 24, delete "source" and replace it with -drain--.

Remarks

This amendment updates the status of the parent application. The applicant's representative is reminded to update the status of the parent via an amendment. In this way the status change of the parent will not be missed upon allowance.

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Allowable Subject Matter

Claims 16-20 are allowed.

The following is an examiner's statement of reasons for allowance: The examiner has reviewed the prior art in light of applicant's claimed invention and finds that the combined claims define over the prior art. The cited prior art does not disclose or suggest a process to form a metal oxide semiconductor transistor of a non-volatile memory inter alia the limitations "....patterning the mask layer, the liner layer and the substrate to form an opening in the substrate; forming a tunnel dielectric layer over the interior surface of the opening; forming a first conductive type pocket doping region within the substrate on the sidewall of the opening; forming a first floating gate and on the sidewalls of the opening; a second floating gate forming a source region in the substrate at the bottom section of the opening; forming an inter-gate dielectric layer inside the opening; forming a first control gate and a second control gate on the sidewalls of the opening such that the first control gate extends to cover the sidewall of the first floating gate and the second control gate extends to cover the sidewall of the second floating gate; removing the mask layer and the liner layer; forming a source region in the substrate; forming a first conductive type second well the second conductive type first well junction between the first conductive type second well region and the second conductive type first well region is at a level higher than the bottom section of the opening; forming an insulating layer in the space between the first region within region such that the control gate and the second control gate and forming a spacer on the sidewall of the first control gate and the second control gate; forming an

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inter-layer dielectric layer over the substrate; forming a contact inside the inter-layer dielectric layer so that the contact connects the drain region with the first conductive type second well region to form a short-circuit; forming a layer such that the conductive layer and the contact are conductive layer over the inter-layer dielectric electrically connected...."

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Chuong A Luu whose telephone number is (571) 272-1902. The examiner can normally be reached on M-F (6:15-2:45).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith can be reached on (571) 272-1907. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

CAL November 22, 2004

> MATTHEW SMITH SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800